

“Epitaxial CVD Growth of Ultra-Thin Si Passivation Layers on Strained Ge Fin Structures”.
Loo R, Arimura H, Cott D, Witters L, Pourtois G, Schulze A, Douhard B, Vanherle W,
Eneman G, Richard O, Favia P, Mitard J, Mocuta D, Langer R, Collaert N, ECS journal of
solid state science and technology 7, P66 (2018). <http://doi.org/10.1149/2.0191802JSS>